

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

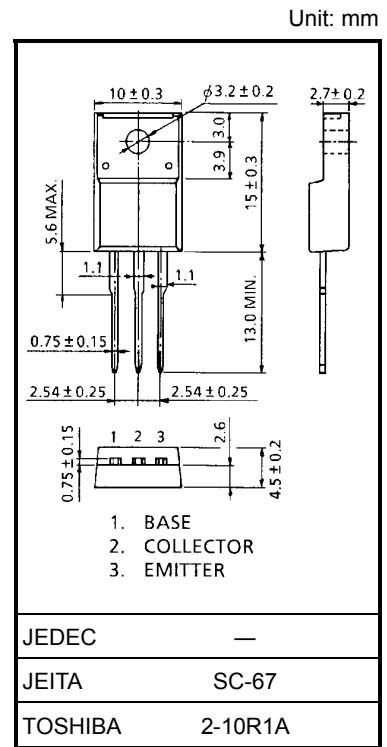
2SC4935

Power Amplifier Applications

- Good h_{FE} linearity
- Complementary to 2SA1869 and 5-watt-output applications.

Maximum Ratings ($T_c = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	3	A
Base current	I_B	0.3	A
Collector power dissipation	P_C	$T_a = 25^\circ\text{C}$	2.0
		$T_c = 25^\circ\text{C}$	10
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to 150	$^\circ\text{C}$



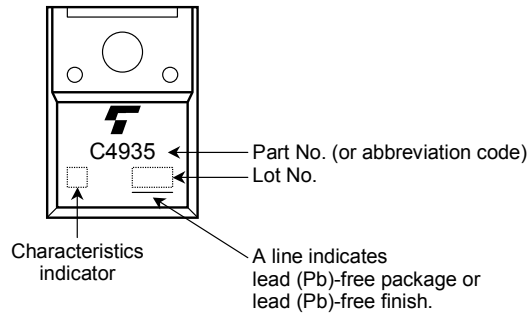
Electrical Characteristics ($T_c = 25^\circ\text{C}$)

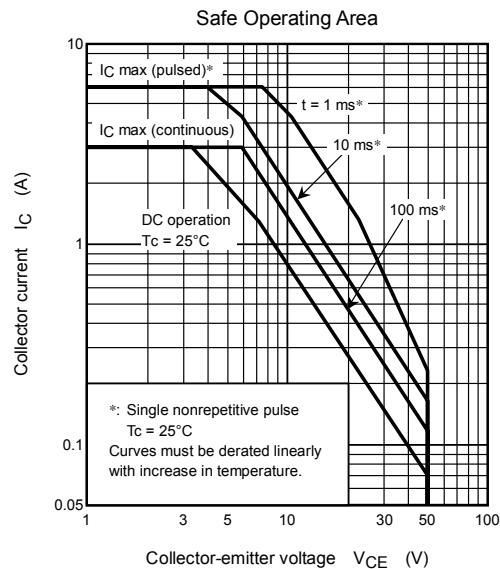
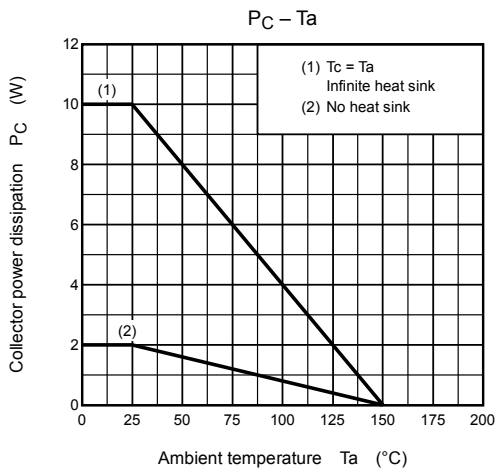
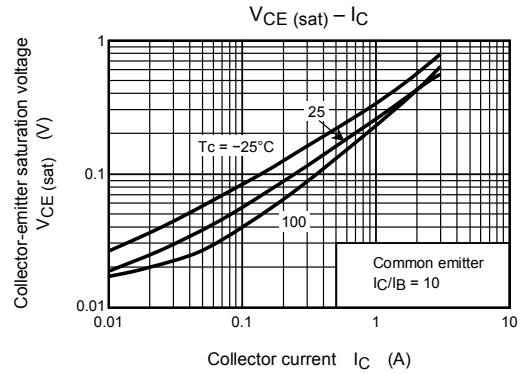
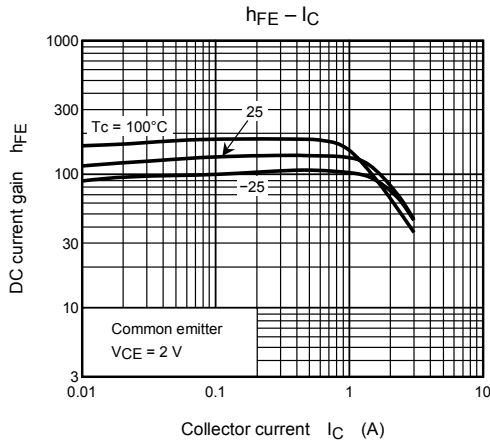
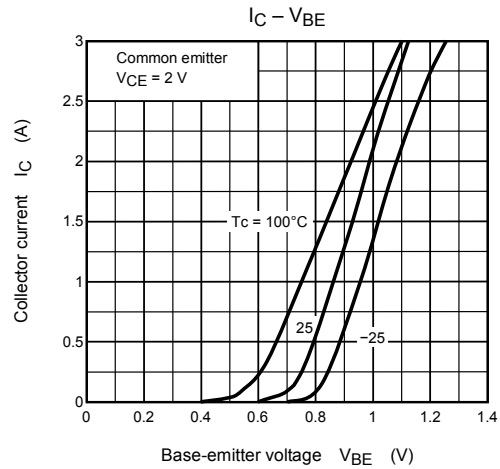
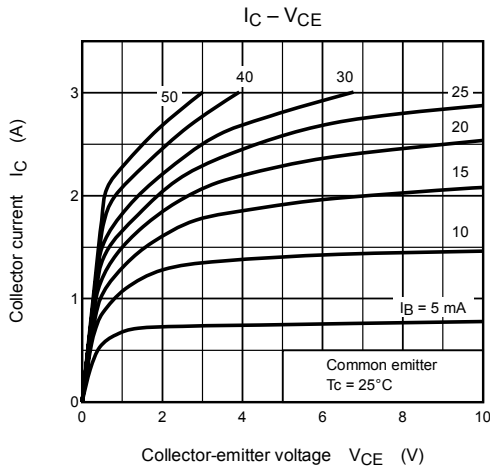
Weight: 1.7 g (typ.)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 50\text{ V}, I_E = 0$	—	—	1.0	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5\text{ V}, I_C = 0$	—	—	1.0	μA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0$	50	—	—	V
DC current gain	$h_{FE(1)}$ (Note)	$V_{CE} = 2\text{ V}, I_C = 0.5\text{ A}$	70	—	240	
	$h_{FE(2)}$	$V_{CE} = 2\text{ V}, I_C = 2.5\text{ A}$	30	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 2\text{ A}, I_B = 0.2\text{ A}$	—	0.4	0.6	V
Base-emitter voltage	V_{BE}	$V_{CE} = 2\text{ V}, I_C = 0.5\text{ A}$	—	0.75	1.0	V
Transition frequency	f_T	$V_{CE} = 2\text{ V}, I_C = 0.5\text{ A}$	—	80	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	30	—	pF

Note: $h_{FE(1)}$ classification O: 70 to 140, Y: 120 to 240

Marking





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